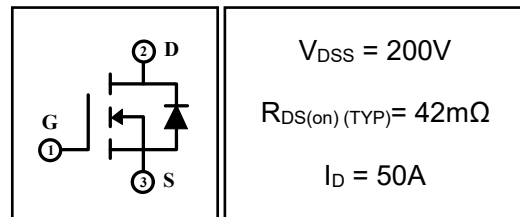


50A 200V N-channel Enhancement Mode Power MOSFET

1 Description

F50N20, the silicon N-channel enhanced vdmofets, is obtained by the self-aligned planar technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. Which accords with the RoHS standard.

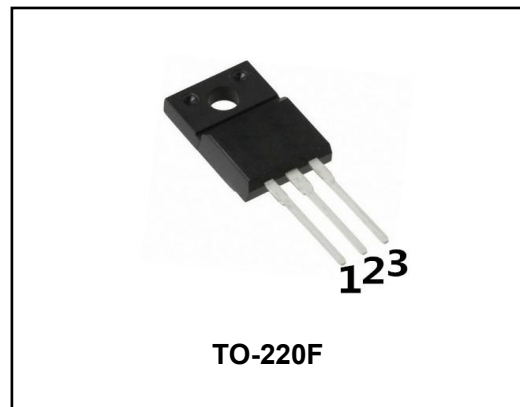


2 Features

- Fast switching
- Low on resistance ($R_{DS(on)} \leq 51m\Omega$)
- Low gate charge (Typ: 49.4nC)
- Low reverse transfer capacitances (Typ: 34pF)
- 100% single pulse avalanche energy test
- 100% ΔV_{DS} test

3 Applications

- High efficiency switch mode power supplies.
- Power switch circuit of adaptor and charger.
- UPS
- Inverter



4 Electrical Characteristics

4.1 Absolute Maximum Rating ($T_C = 25^\circ C$, unless otherwise noted)

Parameter		Symbol	Rating	Units
Drian-to-Source Voltage		V _{DSS}	200	V
Gate-to-Source Voltage		V _{GSS}	±30	V
Continuous Drain Current	T _C =25℃	I _D	50	A
	T _C =100℃		38.5	A
Pulsed Drain Current ⁽¹⁾		I _{DM}	200	A
Single Pulse Avalanche Energy ⁽⁴⁾		E _{AS}	1700	mJ
Peak Diode Recovery dv/dt ⁽⁵⁾		dv/dt	5	V/ns
Power Dissipation	T _a =25℃	P _{tot}	2	W
	T _C =25℃	P _{tot}	75	W
Isolation Voltage		V _{ISO}	2500	V
Junction Temperature Range		T _j	-55～150	℃
Storage Temperature Range		T _{stg}	-55～150	℃
Maximum Temperature for soldering		T _L	300	℃

4.2 Thermal Characteristics

Parameter	Symbol	Rating	Unit
Thermal Resistance, Junction to Case-sink	R_{thJC}	1.67	$^\circ C/W$
Thermal Resistance, Junction to Ambient	R_{thJA}	62.5	$^\circ C/W$

4.3 Electrical Characteristics (T_c=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Value			Units
			Min	Typ	Max	
Off Characteristics						
Drain-to-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	200	--	--	V
Drain-to-Source Leakage Current	I _{DSS}	V _{DS} =200V, V _{GS} =0V, T _C =25℃	--	--	1	μA
		V _{DS} =160V, V _{GS} =0V, T _C =125℃	--	--	100	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±30V	--	--	±100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	--	4	V
Drain-to-Source on-state Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A	--	42	51	mΩ
Forward Transfer Conductance	g _{fs}	V _{DS} =15V, I _D =20A	--	65	--	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz	--	2819	--	pF
Output Capacitance	C _{oss}		--	394	--	
Reverse Transfer Capacitance	C _{rss}		--	34	--	
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	I _D =20A, V _{DD} =100V, V _{GS} =10V, R _G =10Ω	--	35.7	--	nS
Turn-on Rise Time	t _r		--	38.9	--	
Turn-off Delay Time	t _{d(off)}		--	74.4	--	
Turn-off Fall Time	t _f		--	21.9	--	
Total Gate Charge	Q _g	I _D =20A, V _{DD} =160V, V _{GS} =10V	--	49.4	--	nC
Gate-to-Source Charge	Q _{gs}		--	13	--	
Gate-to-Drain(“Miller”) Charge	Q _{gd}		--	18	--	
Drain-Source Diode Characteristics						
Diode Forward Voltage ⁽³⁾	V _{SD}	V _{GS} =0V, I _S =40A	--	--	1.5	V
Diode Forward Current	I _S		--	--	50	A
Reverse Recovery Time ⁽³⁾	t _{rr}	T _J =25℃, I _F =20A, di _F /dt=100A/μS, V _{GS} =0V	--	261	--	nS
Reverse Recovery Charge ⁽³⁾	Q _{rr}		--	2770	--	nC
Reverse Recovery Current ⁽³⁾	I _{RRM}		--	21.2	--	A

Notes:

- 1: Repetitive rating, pulse width limited by maximum junction temperature.
- 2: Surface mounted on FR4 Board, t≤10sec.
- 3: Pulse width ≤ 300μs, duty cycle ≤ 2%.
- 4: L=10mH, I_D=18.5A, V_{DD}=50V, V_{GATE}=200V, Start T_J=25°C.
- 5: I_{SD}=20A, di/dt≤100A/μs, V_{DD}≤BV_{DSS}, Start T_J=25°C.

5 Typical characteristics diagrams

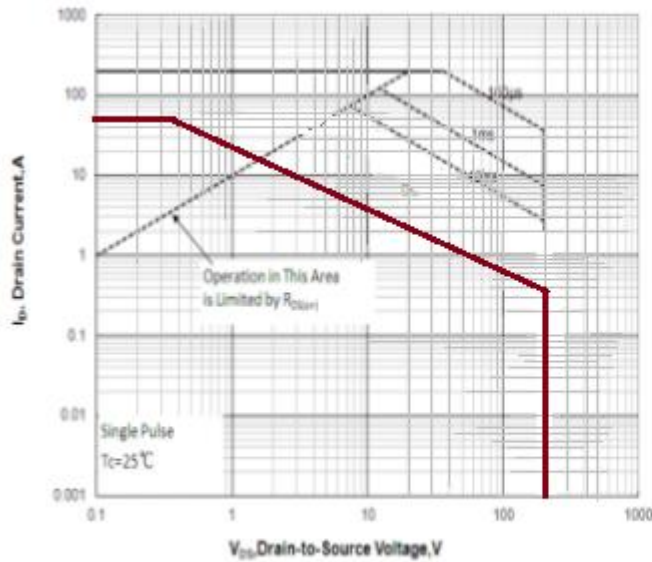


Figure 1 Maximum Forward Bias Safe Operating Area

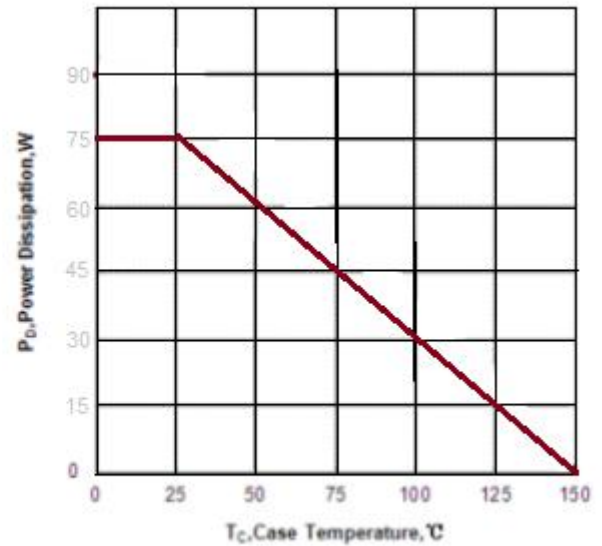


Figure 2 Maximum Power dissipation vs Case Temperature

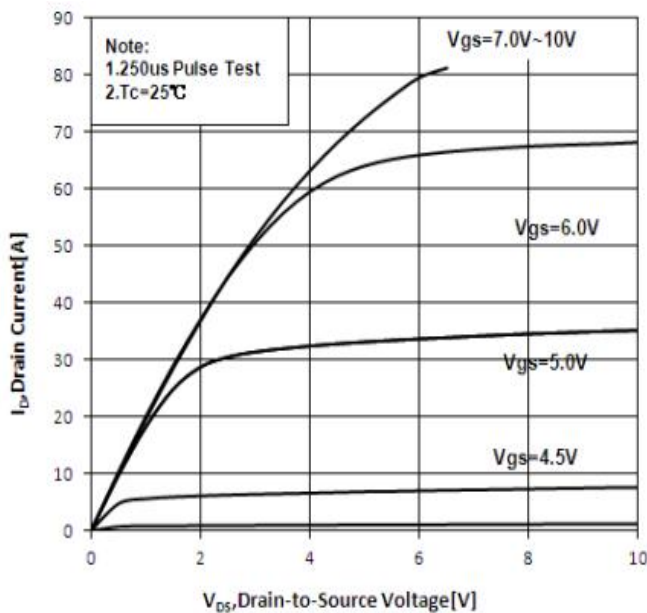


Figure 3 Maximum Continuous Drain Current vs Case Temperature

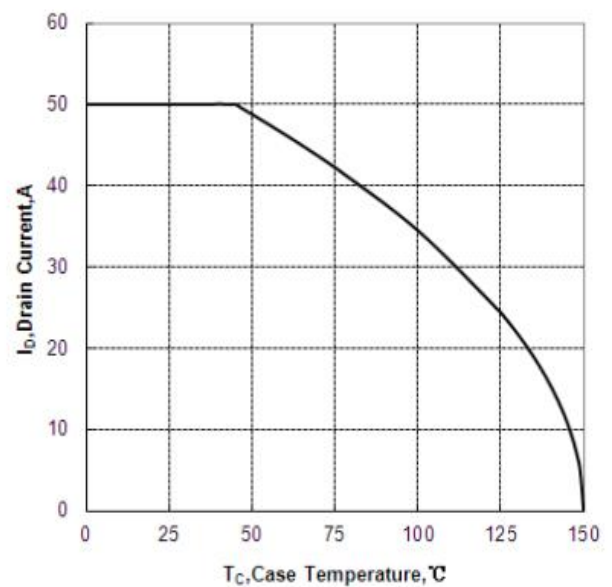


Figure 4 Typical Output Characteristics

5 Typical characteristics diagrams(continues)

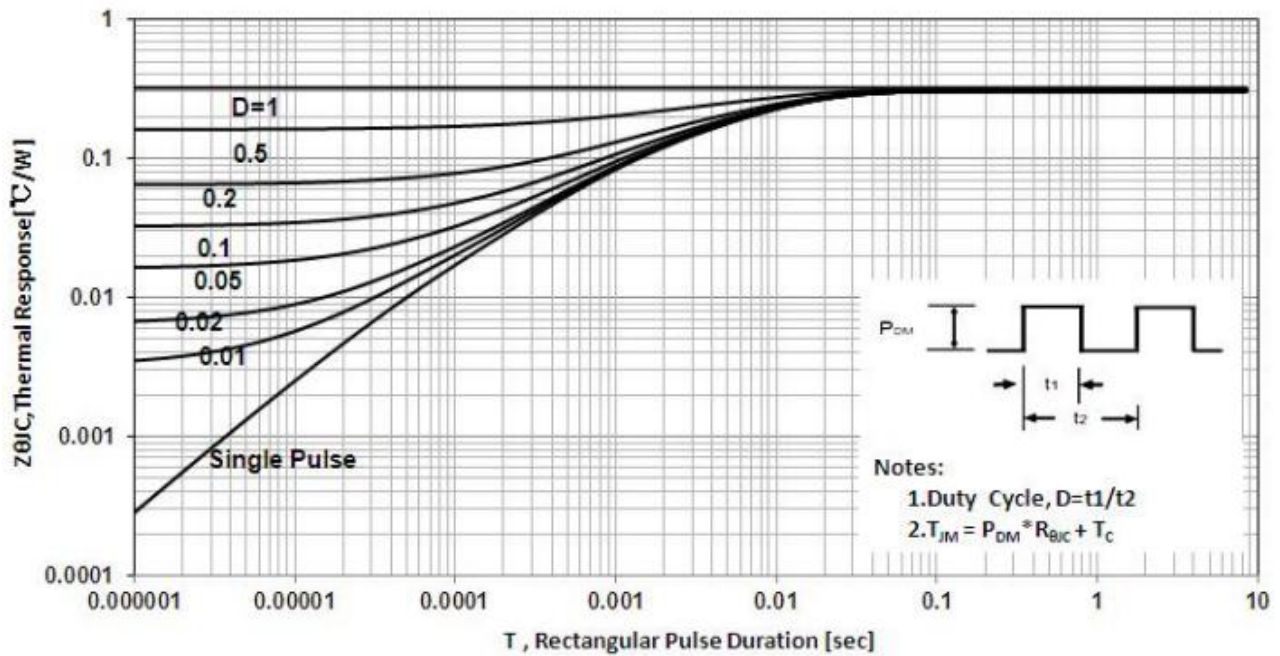


Figure 5 Maximum Effective Thermal Impedance , Junction to Case

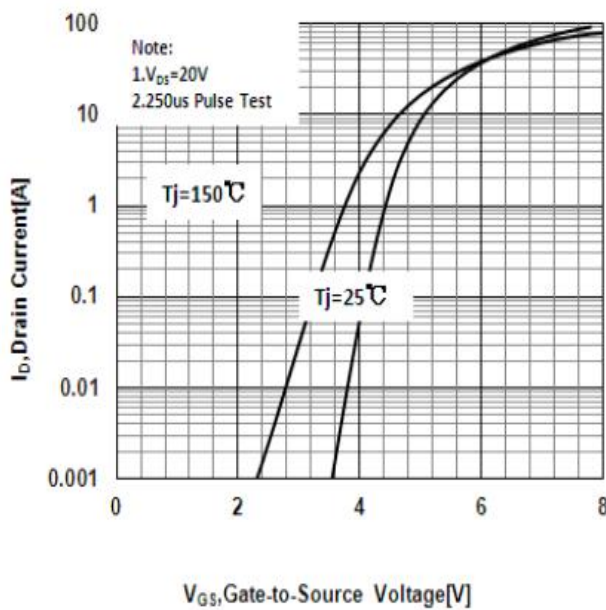


Figure 6 Typical Transfer Characteristics

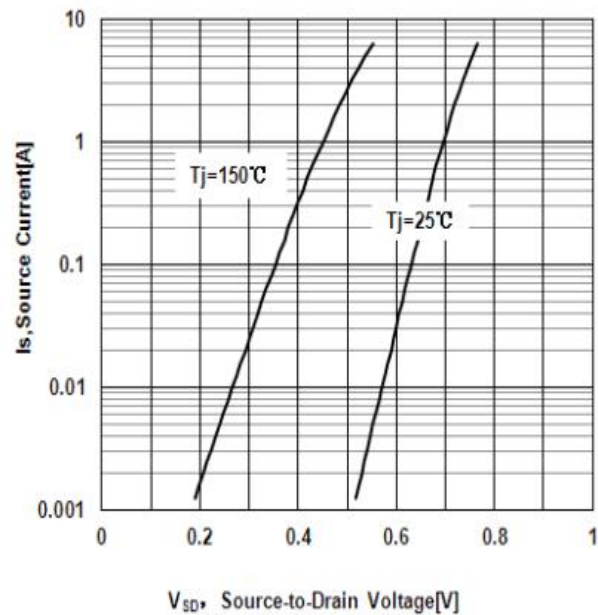


Figure 7 Typical Body Diode Transfer Characteristics

5 Typical characteristics diagrams(continues)

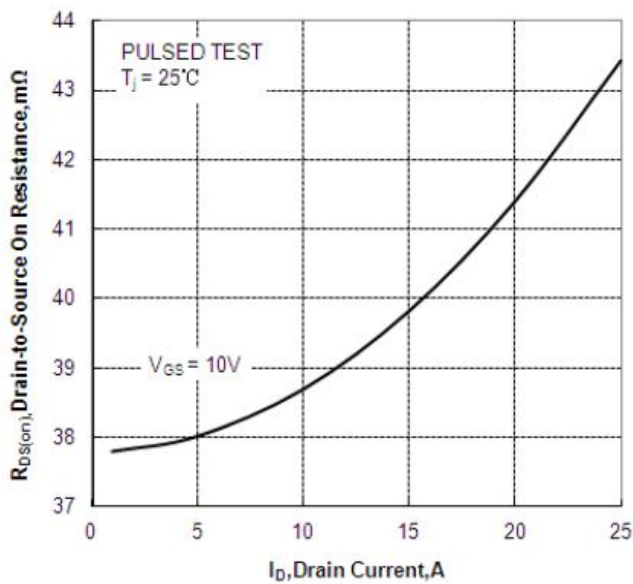


Figure 8 Typical Drain to Source ON Resistance vs Drain Current

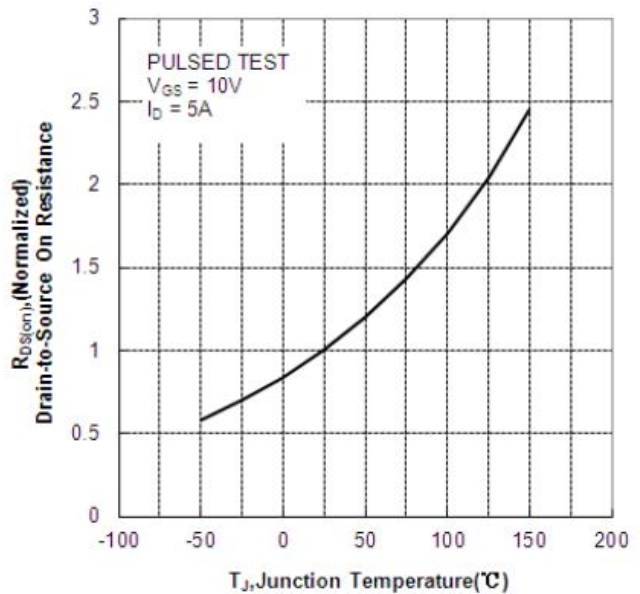


Figure 9 Typical Drain to Source on Resistance vs Junction Temperature

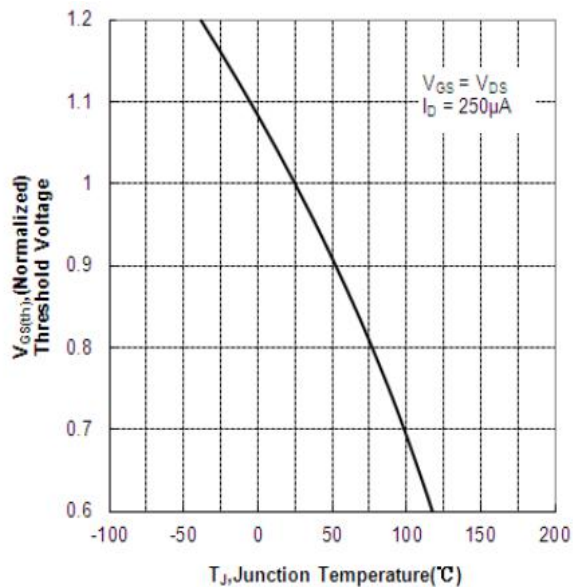


Figure 10 Typical Threshold Voltage vs Junction Temperature

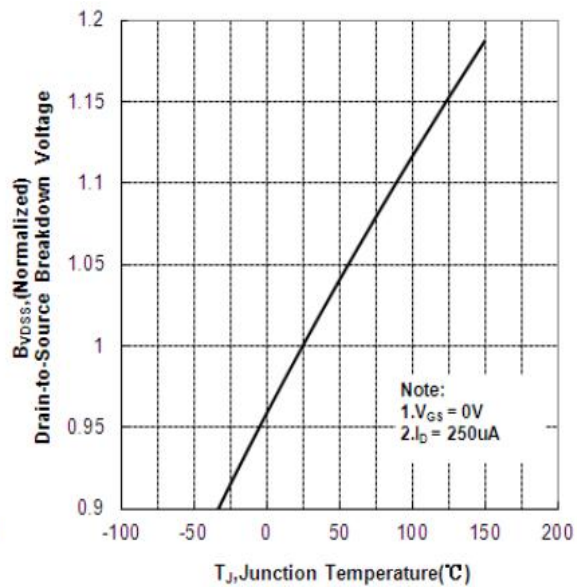


Figure 11 Typical Breakdown Voltage vs Junction Temperature

5 Typical characteristics diagrams(continues)

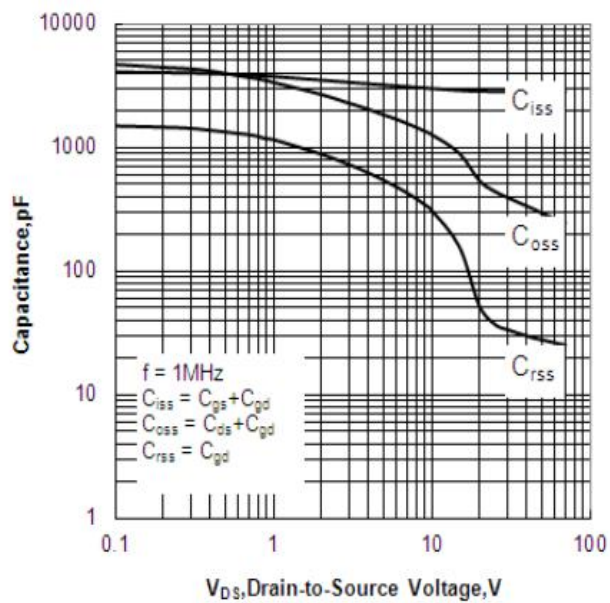


Figure 12 Typical Capacitance vs Drain to Source Voltage

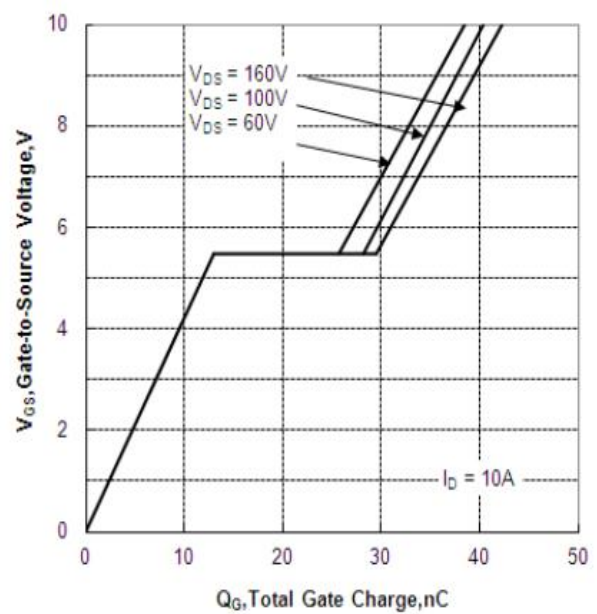
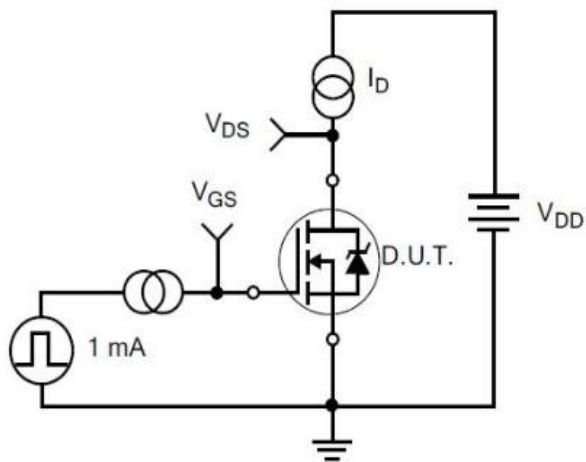
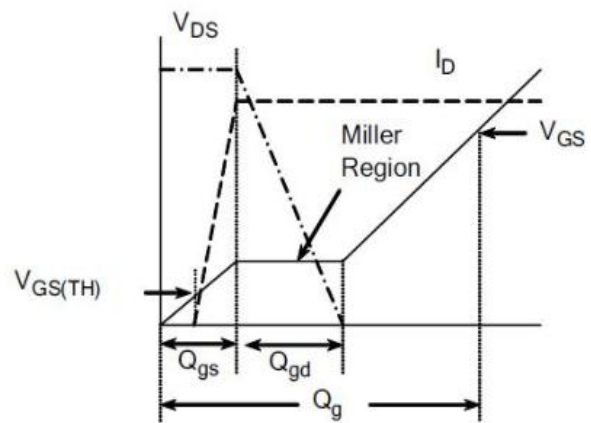


Figure 13 Typical Gate Charge vs Gate to Source Voltage

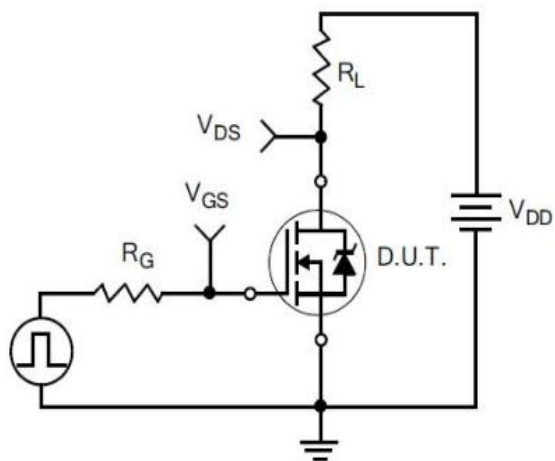
6 Typical Test Circuit and Waveform



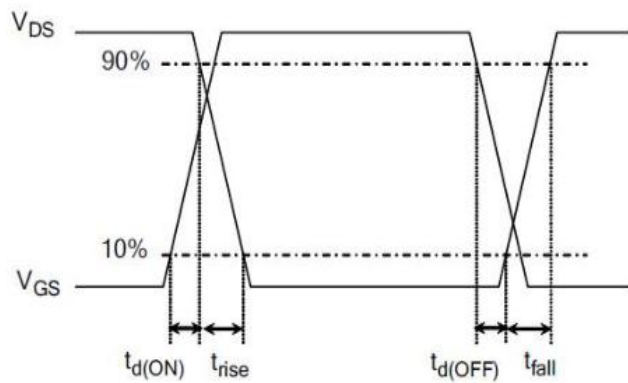
1) Gate Charge Test Circuit



2) . Gate Charge Waveform

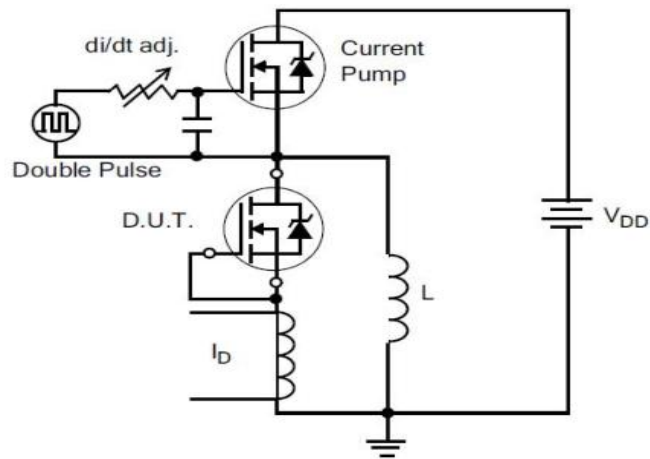


3) Resistive Switching Test Circuit

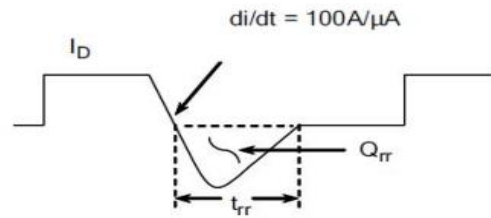


4) Resistive Switching Waveforms

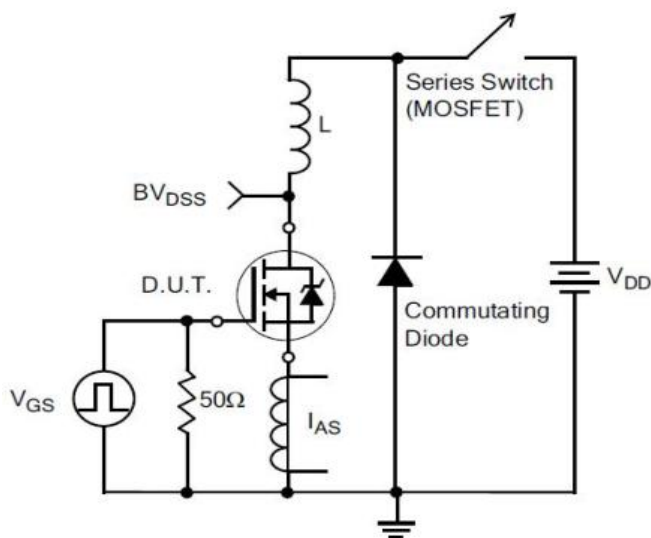
6 Typical Test Circuit and Waveform(continues)



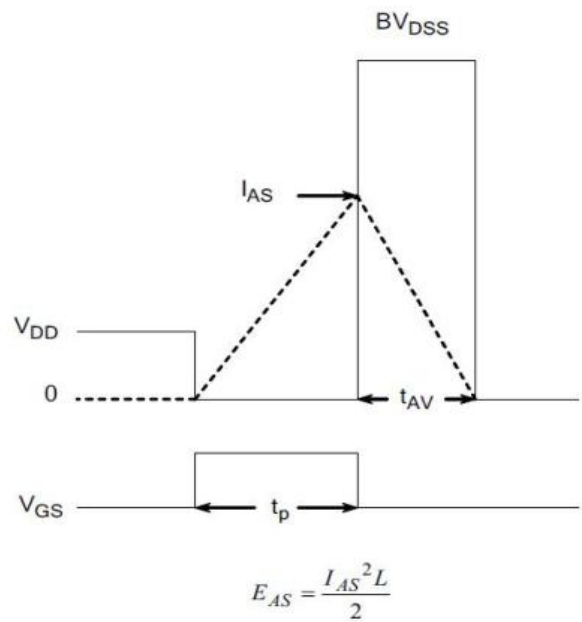
5) Diode Reverse Recovery Test Circuit



6) Diode Reverse Recovery Waveform

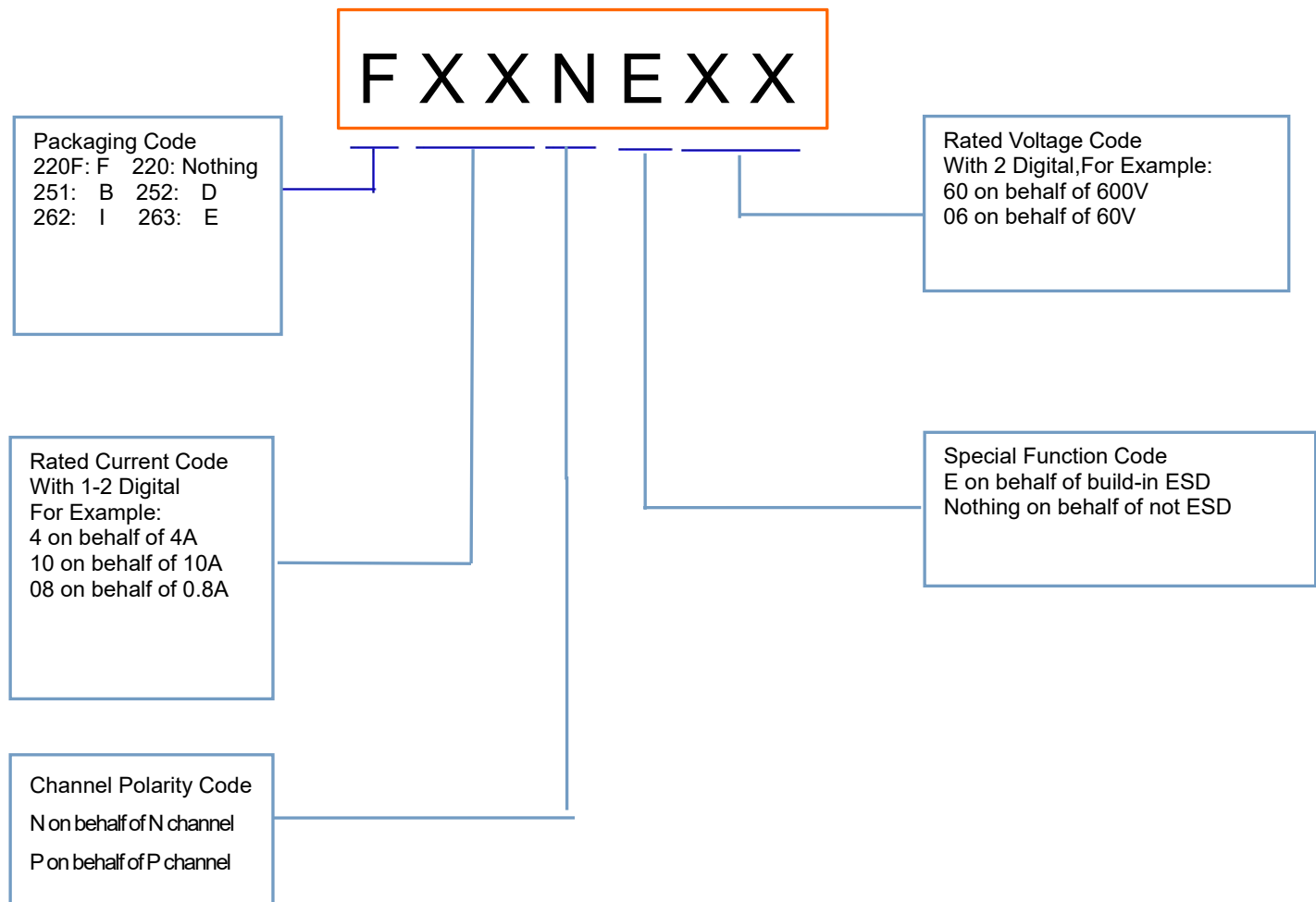


7) . Unclamped Inductive Switching Test Circuit



8) Unclamped Inductive Switching Waveforms

7 Product Names Rules

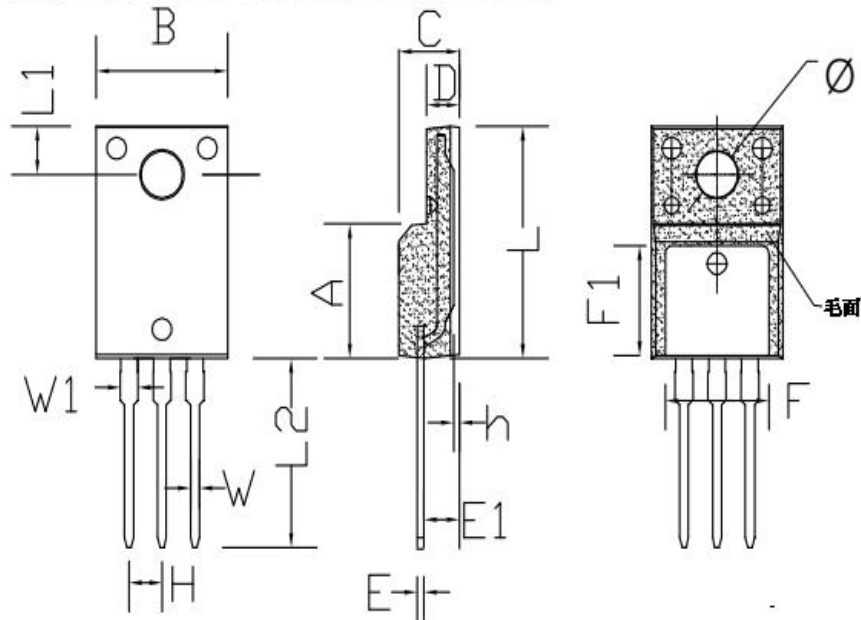


8 Product Specifications and Packaging Models

Product Model	Package Type	Mark Name	RoHS	Package	Quantity
F50N20	TO-220F	F50N20	Pb-free	Tube	1000/box

9 Dimensions

TO-220F PACKAGE OUTLINE DIMENSIONS



Symbol	DimensionsIn Millimeters		DimensionsIn Inches	
	min.	max.	min.	max.
A	8.80	9.30	0.346	0.366
B	10.00	10.50	0.394	0.413
C	4.30	4.90	0.169	0.193
D	2.30	2.70	0.091	0.106
L	15.55	16.15	0.612	0.636
h	0.40	0.60	0.016	0.024
L1	3.15	3.55	0.124	0.140
L2	12.65	13.35	0.498	0.526
W	0.70	0.90	0.028	0.035
W1	1.15	1.55	0.045	0.061
H	2.54 TYP		0.100 TYP	
E	0.48	0.53	0.019	0.021
φ	2.90	3.40	0.114	0.134
E1	2.40	2.90	0.094	0.114
F	7.75	8.25	0.305	0.325
F1	7.35	7.85	0.289	0.309

10 Attentions

- Jiangsu Donghai Semiconductor Technology CO.,LTD. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of Donghai products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

11 Appendix

Revision history:

Date	REV.	Description	Page
2017.07.14	1.0	Original	